

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **TPV375** is a Common Emitter Device Designed for Class A Television Band III Applications.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	8 A
<b>V<sub>CB</sub></b>	65 V
<b>P<sub>DISS</sub></b>	140 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>q<sub>JC</sub></b>	1.5 °C/W

**PACKAGE STYLE .500 4L STUD**

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25,65	1.050/26,67
B	.220/5,59	.230/5,84
C	.495/12,57	.505/12,83
D	.003/0,08	.007/0,18
E	.160/4,06	.180/4,57
F	.622/15,80	
G	.100/2,54	.130/3,31
H	.415/10,54	.425/10,80
I	.720/18,29	
J	.250/6,35	.290/7,37

1 = COLLECTOR    2 & 4 = EMITTER  
3 = BASE

**ORDER CODE: ASI10760**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA			35			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 50 mA	R <sub>BE</sub> = 10 Ω		60			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 50 mA			65			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA			4.0			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V	I <sub>C</sub> = 1.0 A		20		120	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 30 V	f = 1.0 MHz				85	<b>pF</b>
<b>G<sub>PE</sub></b>	V <sub>CE</sub> = 28 V	I <sub>C</sub> = 2.5 A	P <sub>out</sub> = 20 W	8.0	9.0		<b>---</b>
<b>y</b>	f = 225 MHz	VSWR = ∞:1		NO DEGRADATION IN OUTPUT POWER			
<b>IMD<sub>3</sub></b>	V <sub>CE</sub> = 28 V	I <sub>C</sub> = 2.5 A	P <sub>ref</sub> = 14 W			-55	<b>dB</b>
	f = 225 MHz	Vision = -8.0 dB	Snd. = -7.0 dB				
			SB = -16 dB				



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